



#### **60V N-Channel Enhancement Mode MOSFET**

Voltage

60 V

Current

3.2A

#### **Features**

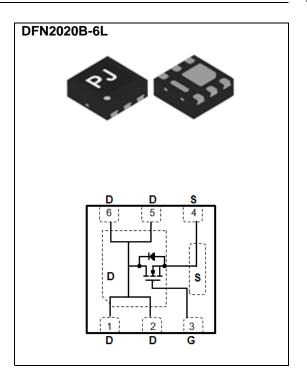
- RDS(ON), VGS@10V, ID@3.2A<75mΩ
- RDS(ON), VGS@4.5V, ID@2.0A<90m $\Omega$
- Advanced Trench Process Technology
- High density cell design for ultra low on-resistance
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

#### **Mechanical Data**

• Case: DFN2020B-6L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0003 ounces, 0.0086 grams



### **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V <sub>DS</sub>	60	V
Gate-Source Voltage		V <sub>GS</sub>	<u>+</u> 20	V
Continuous Drain Current		ID	3.2	Α
Pulsed Drain Current		I <sub>DM</sub>	12.8	Α
Power Dissipation	T <sub>a</sub> =25°C	P <sub>D</sub>	2.4	W
	Derate above 25°C		16	mW/°C
Operating Junction and Storage Temperature Range		T <sub>J</sub> ,T <sub>STG</sub>	-55~175	°C
Typical Thermal Resistance - Junction to Ambient, t<10s (Note 3)		Reja	62.5	°C/W





### **Electrical Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	60	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	1.0	1.8	2.5	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =3.2A	-	53	75	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =2.0A	-	61	90	
Zero Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =48V, V <sub>GS</sub> =0V	-	-	1	uA
Gate-Source Leakage Current	Igss	V <sub>GS</sub> = <u>+</u> 20V, V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 6)						
Total Gate Charge	Qg	V <sub>DS</sub> =48V, I <sub>D</sub> =3.0A, V <sub>GS</sub> =10V (Note 1,2)	-	9.3	-	nC
Gate-Source Charge	Qgs		-	2.2	-	
Gate-Drain Charge	$Q_{gd}$		-	1.9	-	
Input Capacitance	Ciss	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1.0MHZ	-	509	-	pF
Output Capacitance	Coss		-	47	-	
Reverse Transfer Capacitance	Crss		-	23	-	
Turn-On Delay Time	td <sub>(on)</sub>	$\begin{array}{c} V_{DD}{=}30V,\ I_{D}{=}3.0A,\\ V_{GS}{=}10V,\\ R_{G}{=}3.3\Omega\ ^{(Note\ 1,2)} \end{array}$	-	3.2	-	
Turn-On Rise Time	tr		-	9.7	-	
Turn-Off Delay Time	td <sub>(off)</sub>		-	18.5	-	
Turn-Off Fall Time	tf		-	6.4	-	
Drain-Source Diode						
Maximum Continuous Drain-Source			-	-	3.2	А
Diode Forward Current	Is					
Diode Forward Voltage	V <sub>SD</sub>	Is=1A, V <sub>GS</sub> =0V	-	0.75	1.2	V

#### NOTES:

- 1. Pulse width<300us, Duty cycle<2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. The maximum current rating is package limited.
- 4. Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ =25°C.
- 5. R<sub>OJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing.





#### **TYPICAL CHARACTERISTIC CURVES**

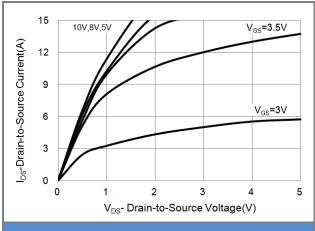
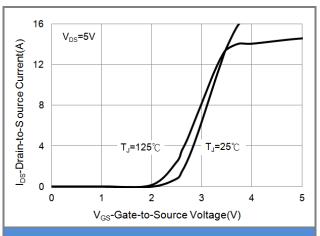


Fig.1 On-Region Characteristics



**Fig.2 Transfer Characteristics** 

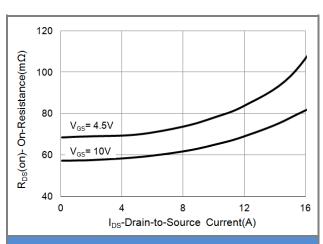


Fig.3 On-Resistance vs. Drain Current

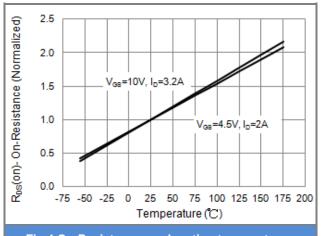


Fig.4 On-Resistance vs. Junction temperature

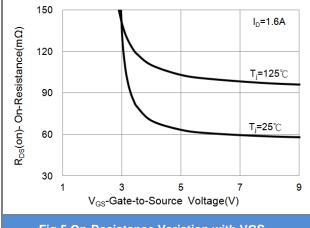
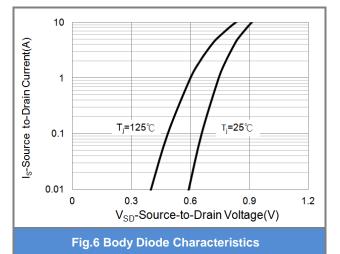


Fig.5 On-Resistance Variation with VGS.







#### **TYPICAL CHARACTERISTIC CURVES**

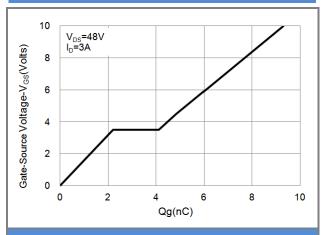


Fig.7 Gate-Charge Characteristics

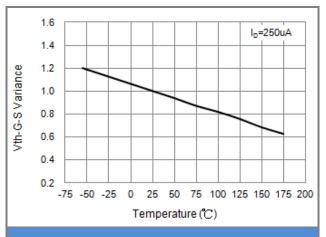


Fig.8 Threshold Voltage Variation with Temperature.

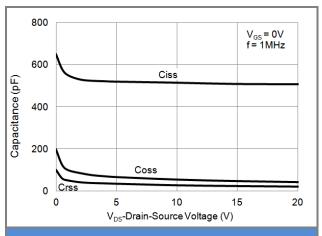


Fig.9 Capacitance vs. Drain-Source Voltage.

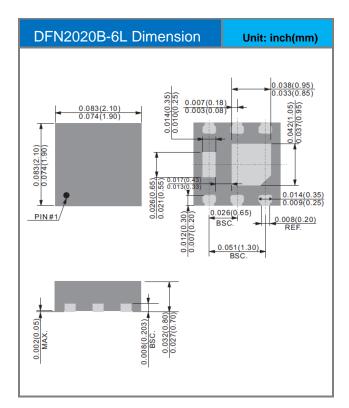


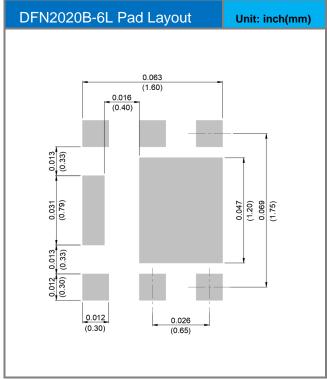


### Part No. Packing Code Version

Part No. Packing Code	Package Type	Packing Type	Marking	Version
PJQ2460-AU_R1_000A1	DFN2020B-6L	3K pcs / 7" reel	460	Halogen free RoHS compliant

### **Packaging Information & Mounting Pad Layout**









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